2024년 1월 26일(금), 15:40-17:25
Room K(205),2층

G. Device & Process Modeling, Simulation and Reliability 분과

[FK3-G] Device Characterization & Modeling II

좌장: 신홍식 수석(DB하이텍), 최성진 교수(국민대학교)

FK3-G-1 15:40-15:55	Effect of Oxygen Content on the Density of States and Lateral Profile of Dopant Concentration in InGaZnO FETs regarding Oxygen Scavenging Seong Hoon Jeon, Won Jung Kim, Changwook Kim, Jong-Ho Bae, Sung-Jin Choi, Dong Myong Kim, and Dae Hwan Kim School of Electrical Engineering, Kookmin University
FK3-G-2 15:55-16:10	Characterization of the Effects of Hydrogen and Oxygen Contents on Current Stress-induced Instability in the Sub-micron Amorphous InGaZnO Thin-film Transistors based on the AC Bias Real-time Current Probe Do Hun Kim[1], Jingyu Park[1], Seoung Joo Myoung[1], Sangwook Kim[2], Kwang-Hee Lee[2], Jee-Eun Yang[2], Younjin Jang[2], and Dae Hwan Kim[1] [1]School of Electrical Engineering, Kookmin University, [2]SAIT
FK3-G-3 16:10-16:25	Abnormal Hump Characteristic under Gated-Diode Pulse Stress and its Oxygen Content Effect in Sub-Micron IGZO TFTs Su Han Noh[1], Jingyu Park[1], Seoung Joo Myoung[1], Sangwook Kim[2] , Kwang-Hee Lee[2] , Jee-Eun Yang[2] , Younjin Jang[2], and Dae Hwan Kim[1] [1]School of Electrical Engineering, Kookmin University, [2]SAIT
FK3-G-4 16:25-16:40	Annealing Process for Improving Electrical Properties of a-IGZO TFTs with Underlap-channel So-Jeong Park[1], Hanbin Lee[1], Jeonghee Ko[1], Yulim An[1], Hyo-In Yang[1], Gyoung-Su Min[1], Jun-Ho Jang[1], Jeong-Yeon Im[1], Dong Myong Kim[1], Dae Hwan Kim[1], Jong-Ho Bae[1], Min-Ho Kang[2], and Sung-Jin Choi[1] [1]School of Electrical Engineering, Kookmin University, [2]Department of Nano-process, NNFC
FK3-G-5 16:40-16:55	Highly Reliable Hump-free Multiple Channel a-InGaZnO Thin-film Transistor on 8-inch Wafer Hyo-In Yang[1], Hanbin Lee[1], Jeonghee Ko[1], Yulim An[1], Gyoung-Su Min[1], So-Jeong Park[1], Jun-Ho Jang[1], Jeong-Yeon Im[1], Dong Myong Kim[1], Dae Hwan Kim[1], Jong-Ho Bae[1], Min-Ho Kang[2], and Sung-Jin Choi[1] [1]School of Electrical Engineering, Kookmin University, [2]Department of Nano-process, NNFC

FK3-G-6 16:55-17:10	Quantitative Analysis based on Subgap Density-of-States (DOS) for Deuterium Annealing Effect in a-IGZO TFTs by TCAD and Experimental Characterization Seongbin Lim[1], Hyeonjun Song[1], Jaewook Yoo[1], Hongseung Lee[1], Soyeon Kim[1], Jo Hak Jeong[1], Kiyoung Lee[3], Hyeon-Sik Jang[1], Minah Park[1], Seohyeon Park[1], Keun Heo[1], Jun-Young Park[2], Yoon Kyeung Lee[1], and Hagyoul Bae[1] [1]Jeonbuk National University, [2]Chungbuk National University, [3]Hongik University
FK3-G-7 17:10-17:25	Low-Frequency Noise and DC I-V Characterization for IrradiationInduced Degradation and Trap Behaviors in a-IGZO TFTs Hongseung Lee[1], Jaewook Yoo[1], Hyeonjun Song[1], Soyeon Kim[1], Seongbin Lim[1], Seohyeon Park[1], Minah Park[1], Kiyoung Lee[2], Yoon Kyeung Lee[1], Keun Heo[1], and Hagyoul Bae[1] [1]Jeonbuk National University, [2]Hongik University